

FIG. 1

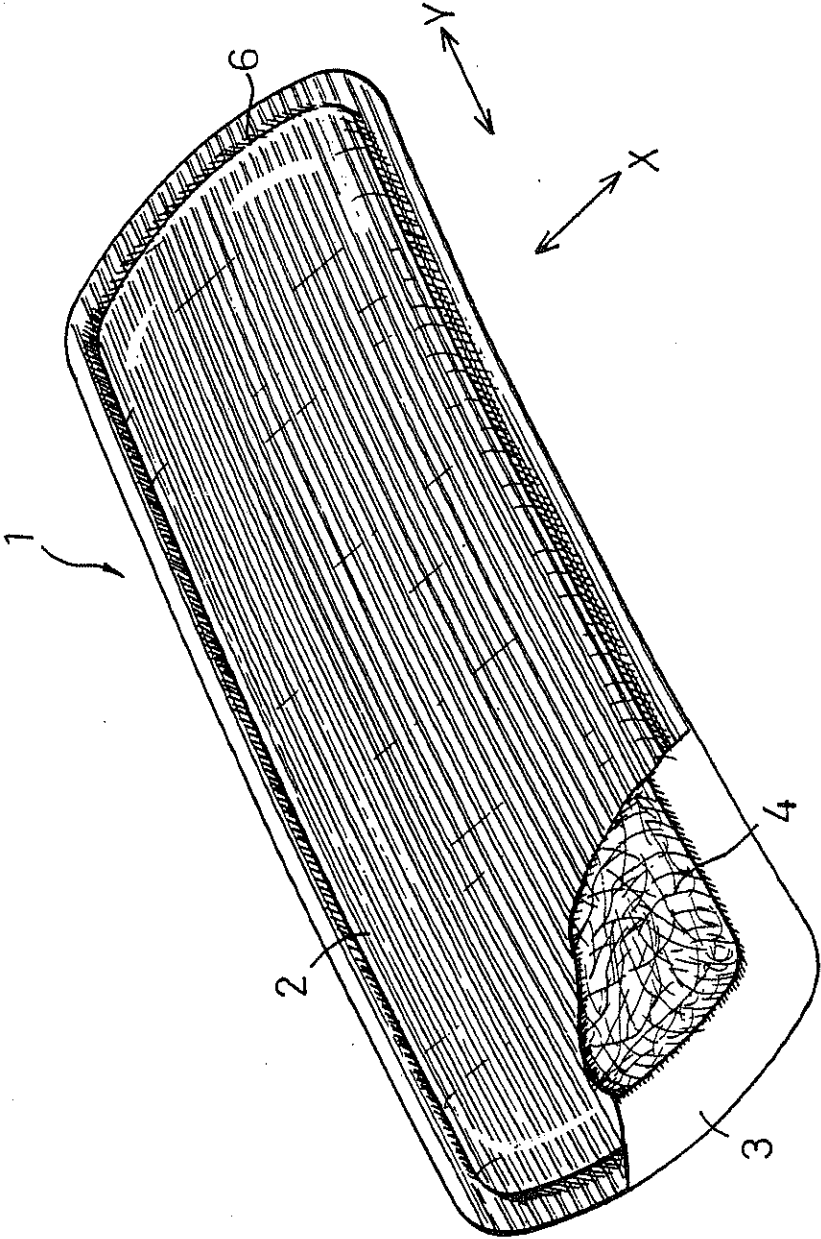
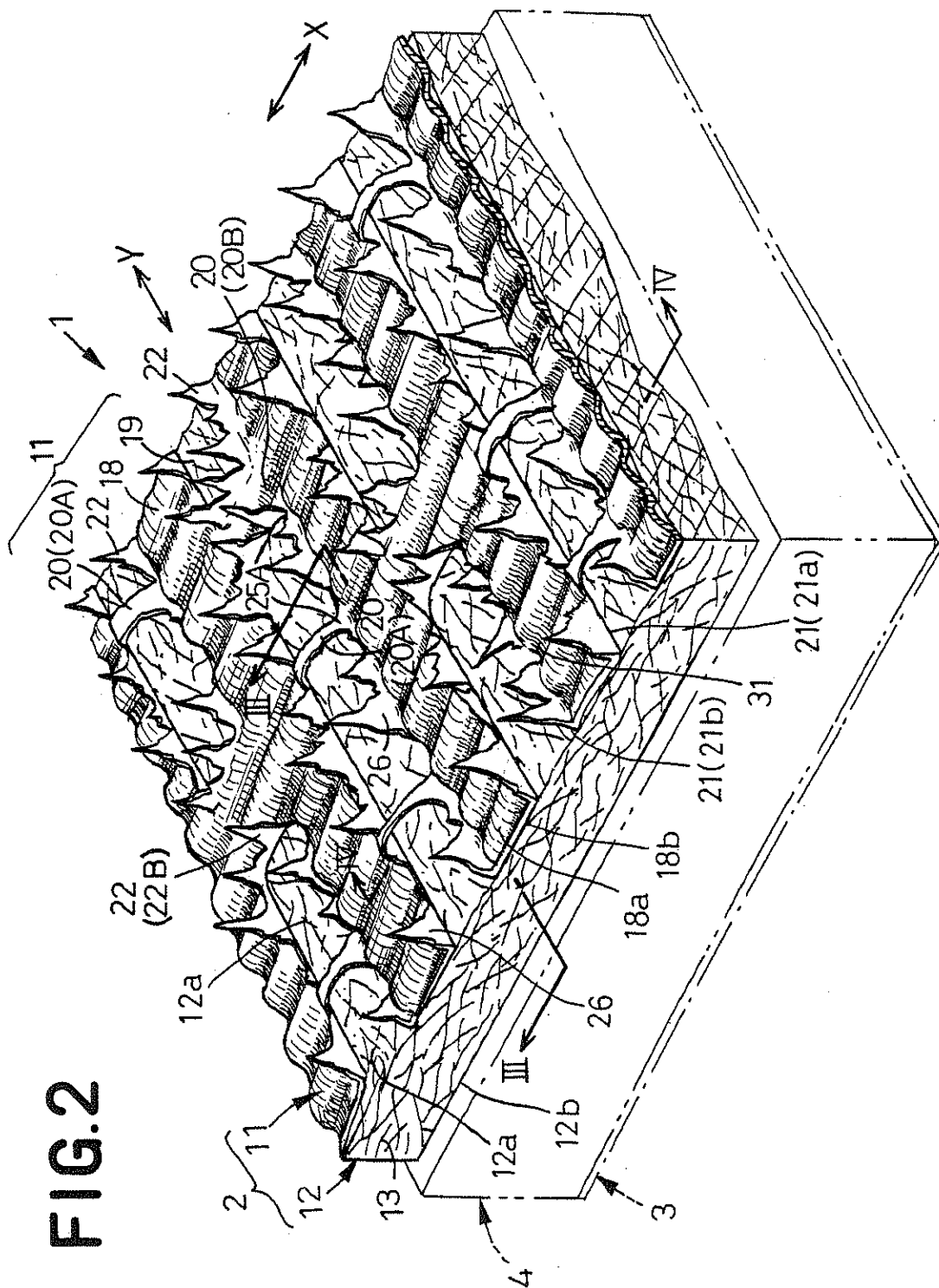


FIG.2



[illegible]

A cross-sectional view of a semiconductor device. The device consists of a substrate 13 with a layered structure. The layers are labeled 11 and 12, with 12 further divided into 12a and 12b. A top layer 18 is patterned into a series of ridges and valleys. The ridges are labeled 18a and 19, and the valleys are labeled 18b. A layer 20 (20A) is formed on top of the ridges, and a layer 22 (22B) is formed on top of the valleys. A layer 21 is formed on top of the ridges, and a layer 27 is formed on top of the valleys. The width of the ridges is labeled W2, and the width of the valleys is labeled W1. The overall width of the device is labeled 2.

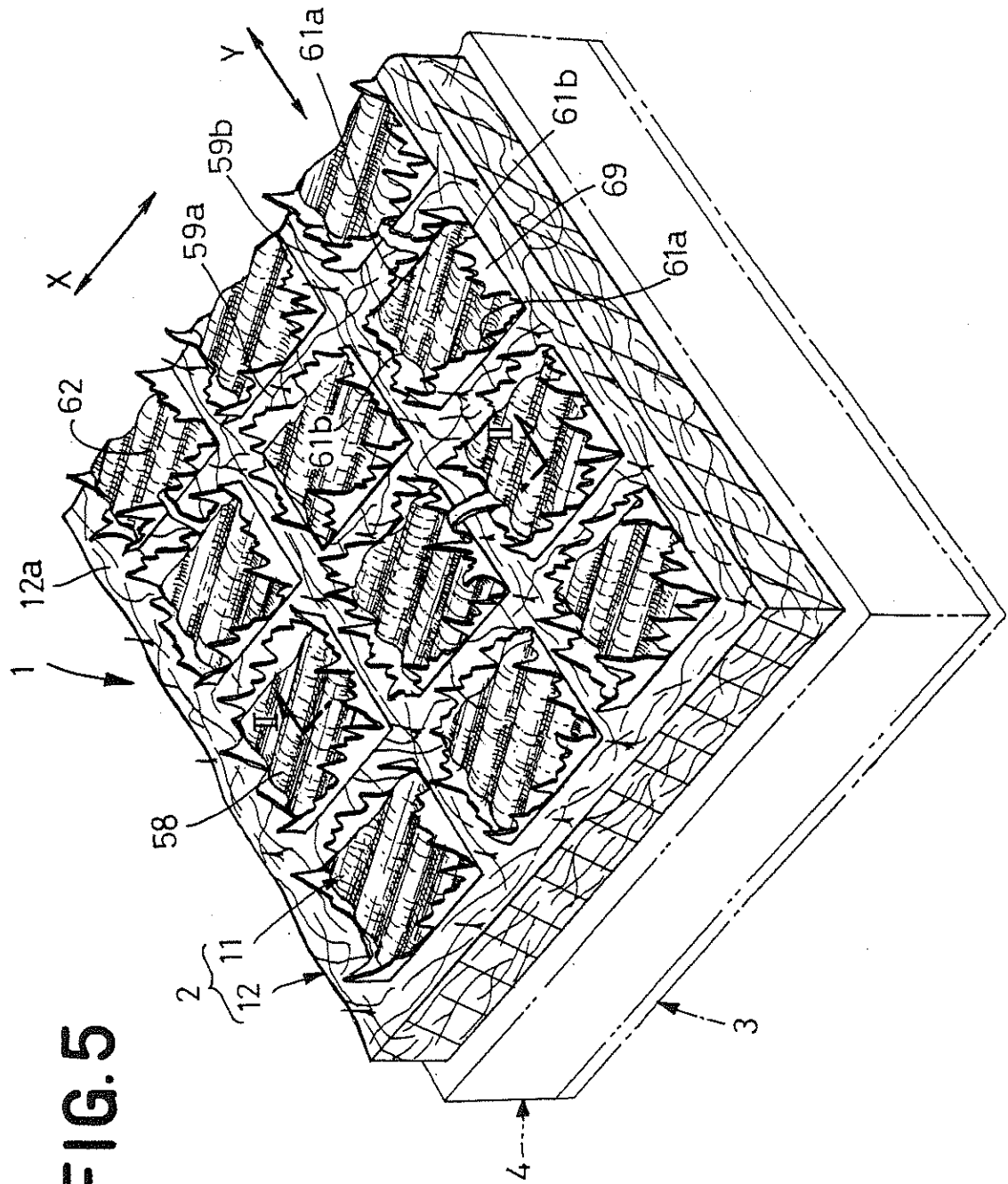


FIG. 6

